

## 1. General description

AC Thyristor Triac power switch in a SOT186A (T0-220F) “full pack” plastic package with self-protection clamping capabilities against low and high energy transients.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Pin compatible with standard triacs
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$  and IEC 61000-4-4 fast transient
- Enhanced dynamic performance
- Package is RoHS compliant
- Package meets UL94V0 flammability requirement
- Package meets UL1557 isolation test requirement rated at 2500V RMS

## 3. Applications

- Fan motor circuits
- Highly inductive, resistive and safety loads
- Loads such as contactors, circuit breakers, valves, dispensers and door locks
- Pump motor circuits

## 4. Quick reference data

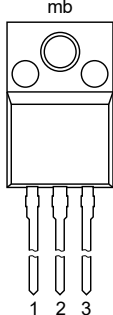
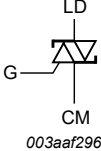
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 89\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	6	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	66	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	60	A
$T_j$	junction temperature		-	-	125	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>PP</sub>	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; Fig. 6	-	-	2	kV
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; Fig. 8	5	-	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; Fig. 8	5	-	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; Fig. 8	5	-	35	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; Fig. 10	-	-	40	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 8 A; T <sub>j</sub> = 25 °C; Fig. 11	-	-	1.65	V
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	800	-	-	V
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	1500	-	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 6 A; dV <sub>com</sub> /dt = 20 V/μs; (snubberless condition); gate open circuit	12	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 6 A; dV <sub>com</sub> /dt = 10 V/μs; gate open circuit	15	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 6 A; dV <sub>com</sub> /dt = 1 V/μs; gate open circuit	20	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p style="text-align: center;">mb</p> <p style="text-align: center;">1 2 3</p> <p style="text-align: center;"><b>TO-220F (SOT186A)</b></p>	 <p style="text-align: center;">LD</p> <p style="text-align: center;">G</p> <p style="text-align: center;">CM</p> <p style="text-align: center;">003aaf296</p>
2	LD	load		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACTT6X-800CN	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 7. Marking

Table 4. Marking codes

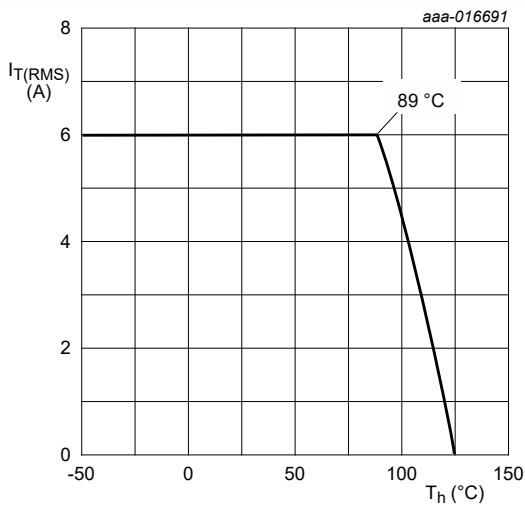
Type number	Marking code
ACTT6X-800CN	ACTT6X-800CN

### 8. Limiting values

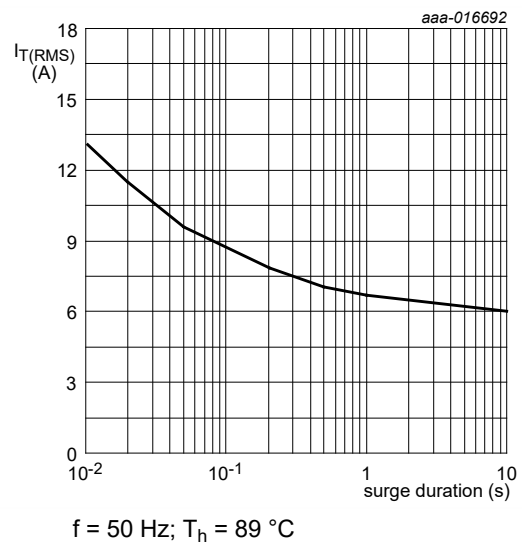
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 89\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	6	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$	-	66	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	60	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	18	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current	$t = 20\text{ }\mu\text{s}$	-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_j$	junction temperature		-	125	$^\circ\text{C}$
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ }^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	2	kV



**Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values**



**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

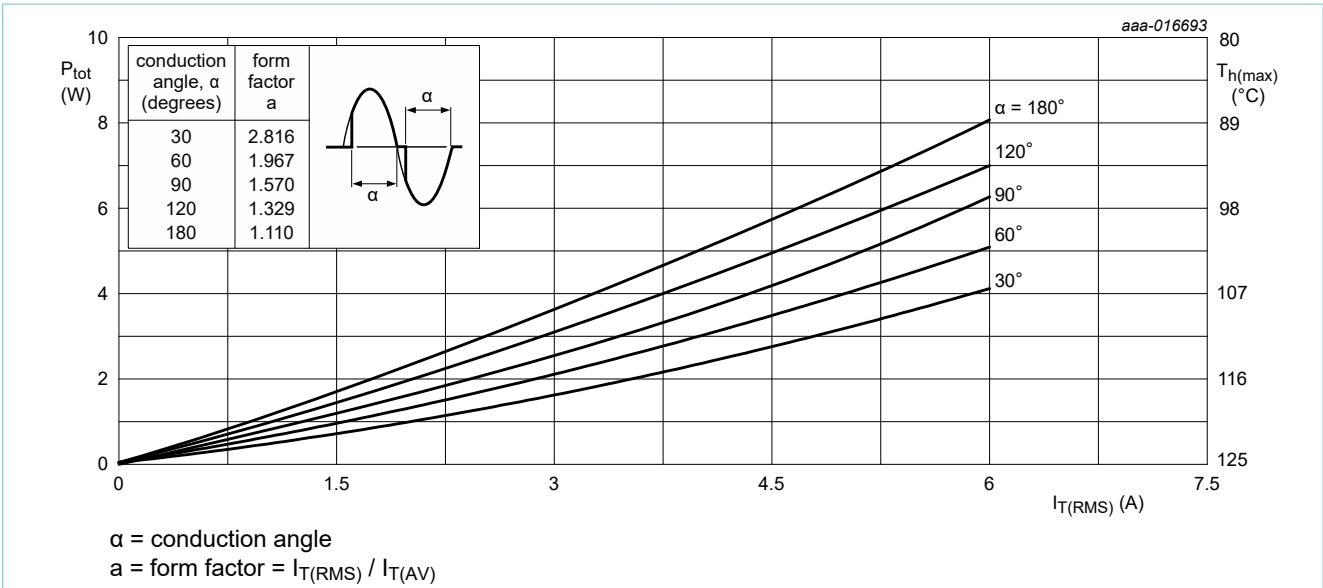


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

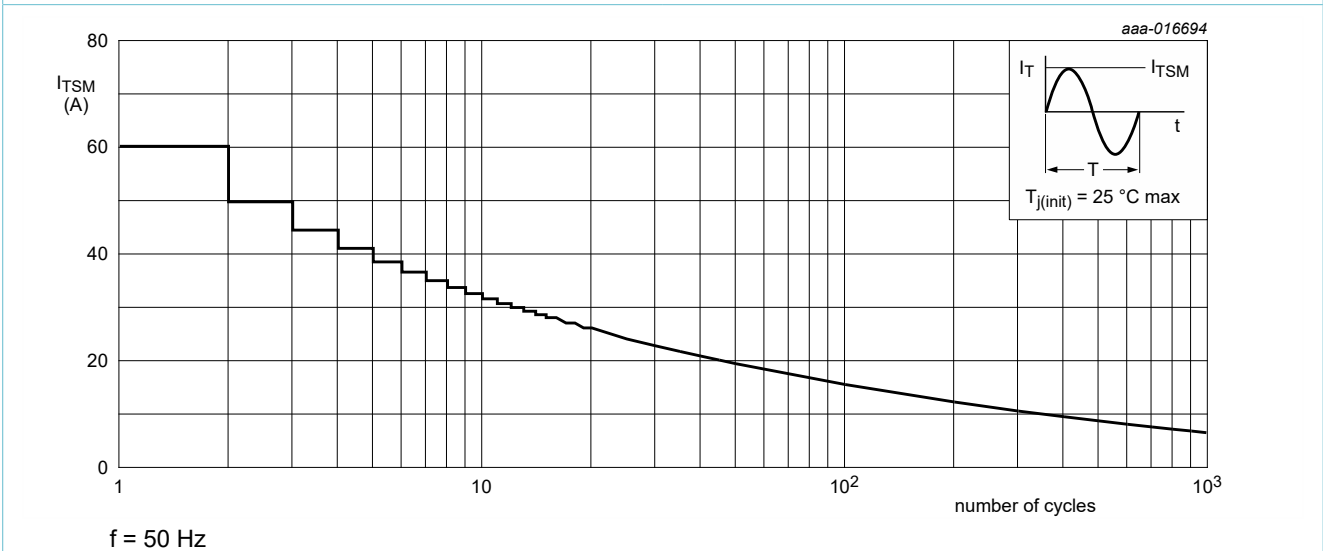


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

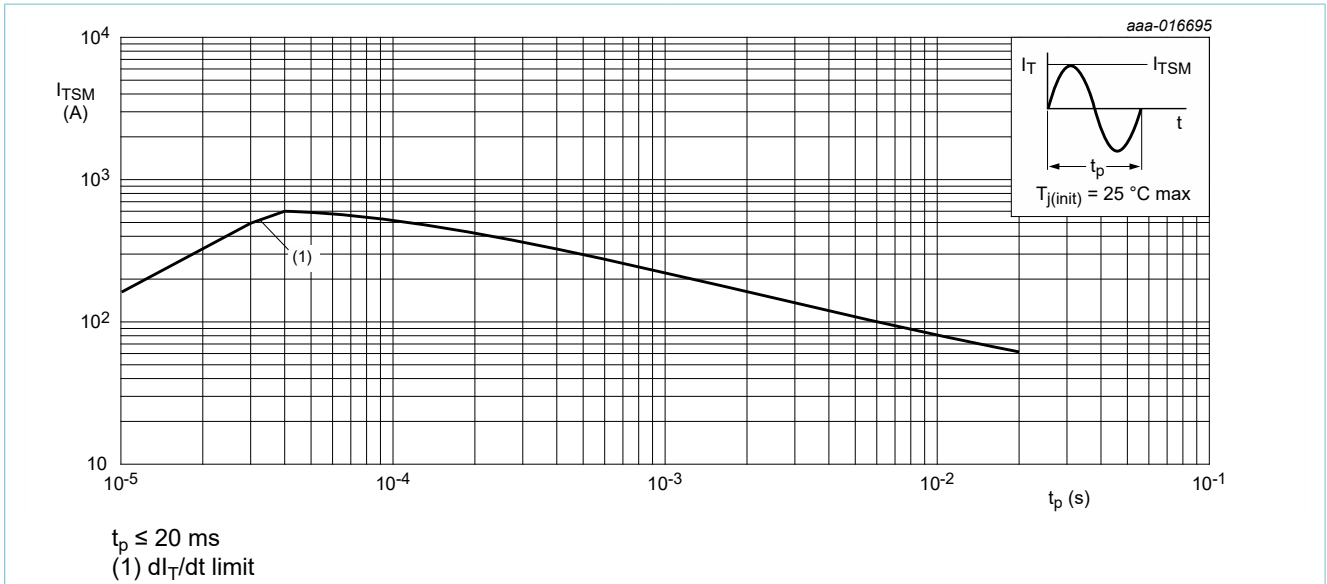


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

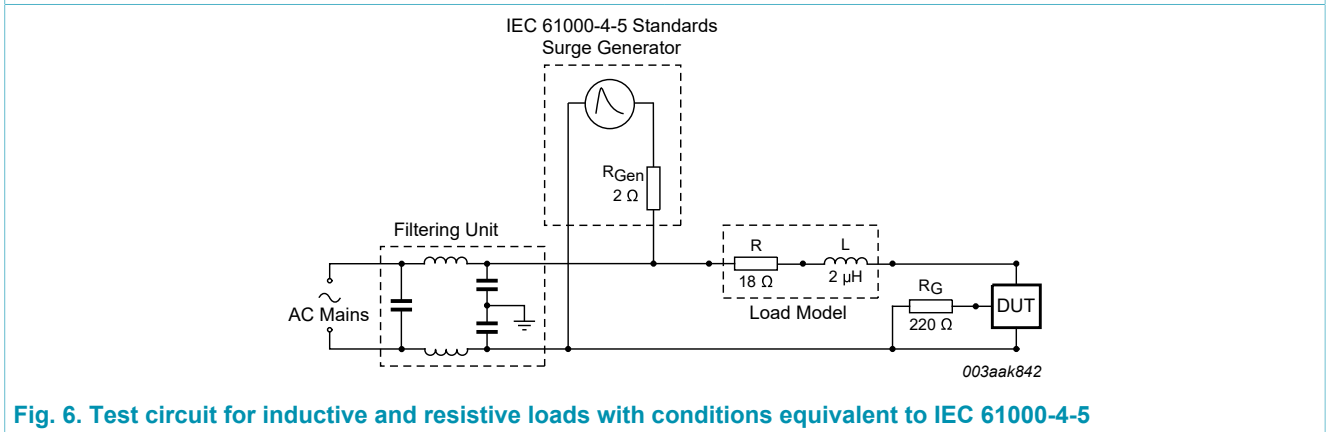


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	full or half cycle; with heatsink compound; <a href="#">Fig. 7</a>	-	-	4.5	K/W
		full or half cycle; without heatsink compound	-	-	6.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

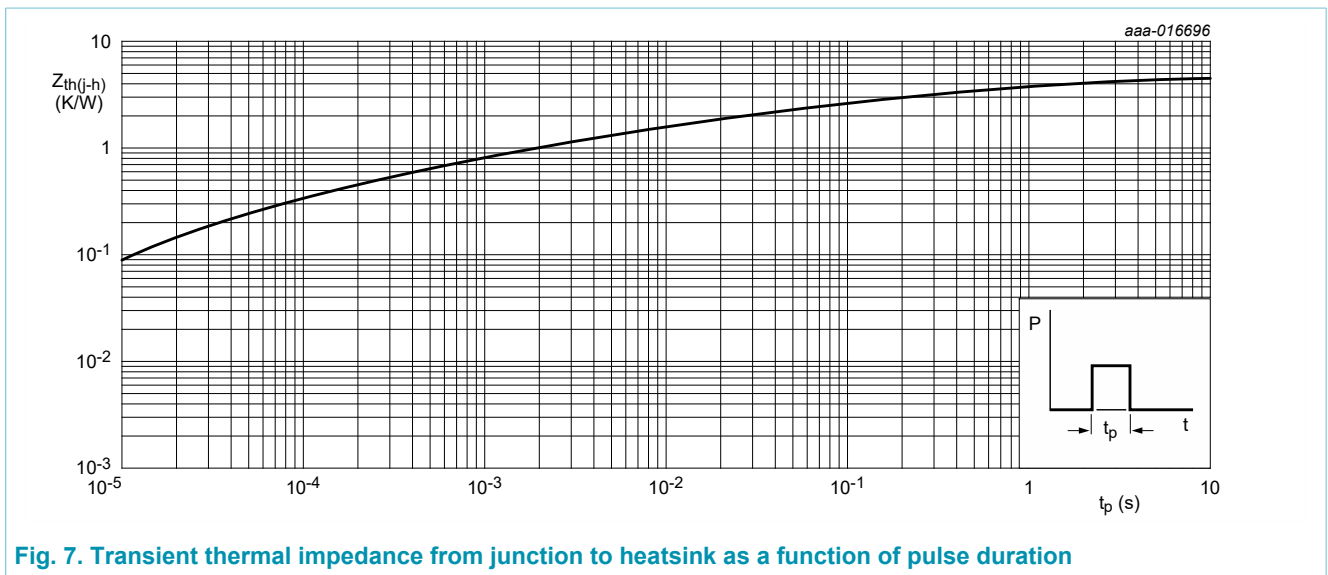


Fig. 7. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 10. Isolation characteristics

Table 7. Isolation characteristics

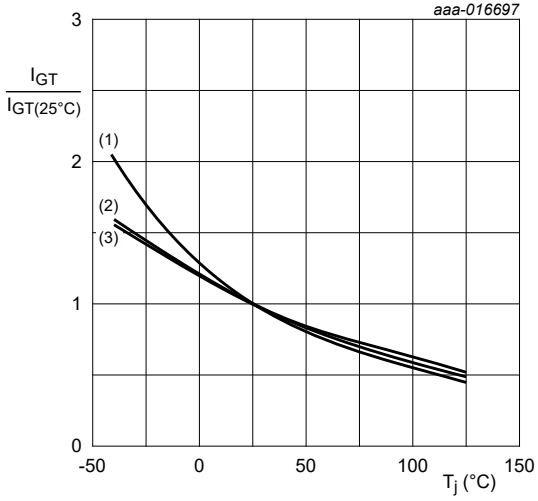
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

## 11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	5	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	5	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	5	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	75	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	50	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	40	mA
$V_T$	on-state voltage	$I_T = 8\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	-	1.65	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	-	0.8	1	V
		$V_D = 400\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 12</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}$ ; $T_j = 125\text{ °C}$	-	-	0.5	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ °C}$	800	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	1500	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	12	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	15	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	20	-	-	A/ms





- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 8. Normalized gate trigger current as a function of junction temperature

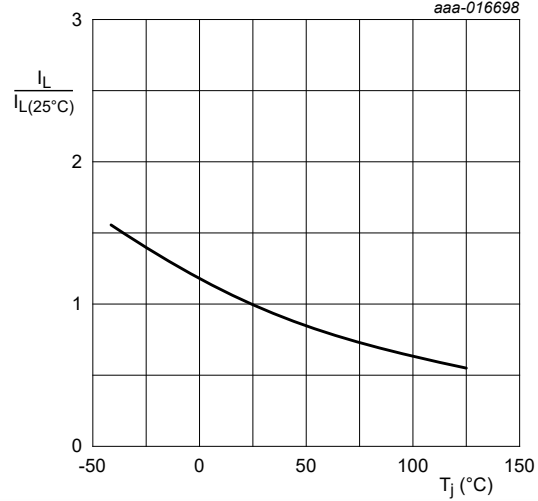


Fig. 9. Normalized latching current as a function of junction temperature

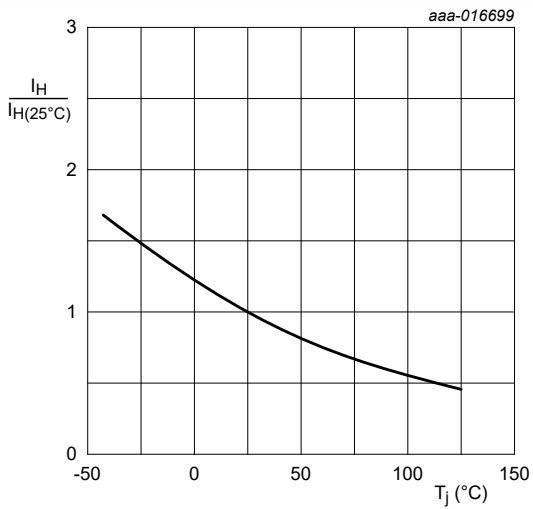
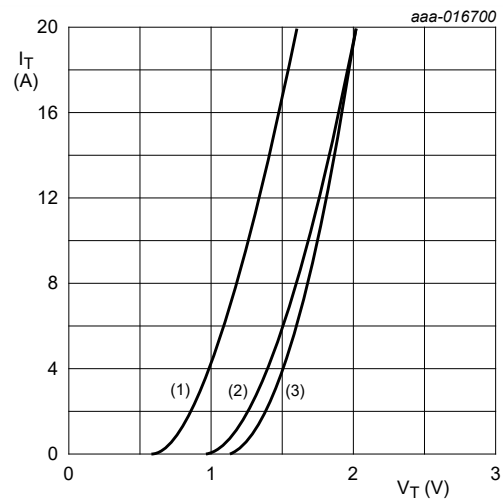


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 1.239 \text{ V}; R_s = 0.037 \Omega$

- (1)  $T_j = 125^\circ\text{C}$ ; typical values
- (2)  $T_j = 125^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 11. On-state current as a function of on-state voltage

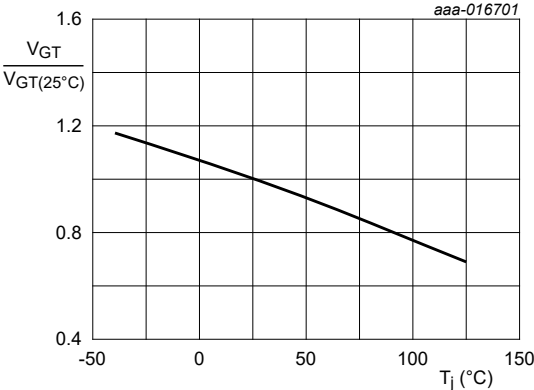


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

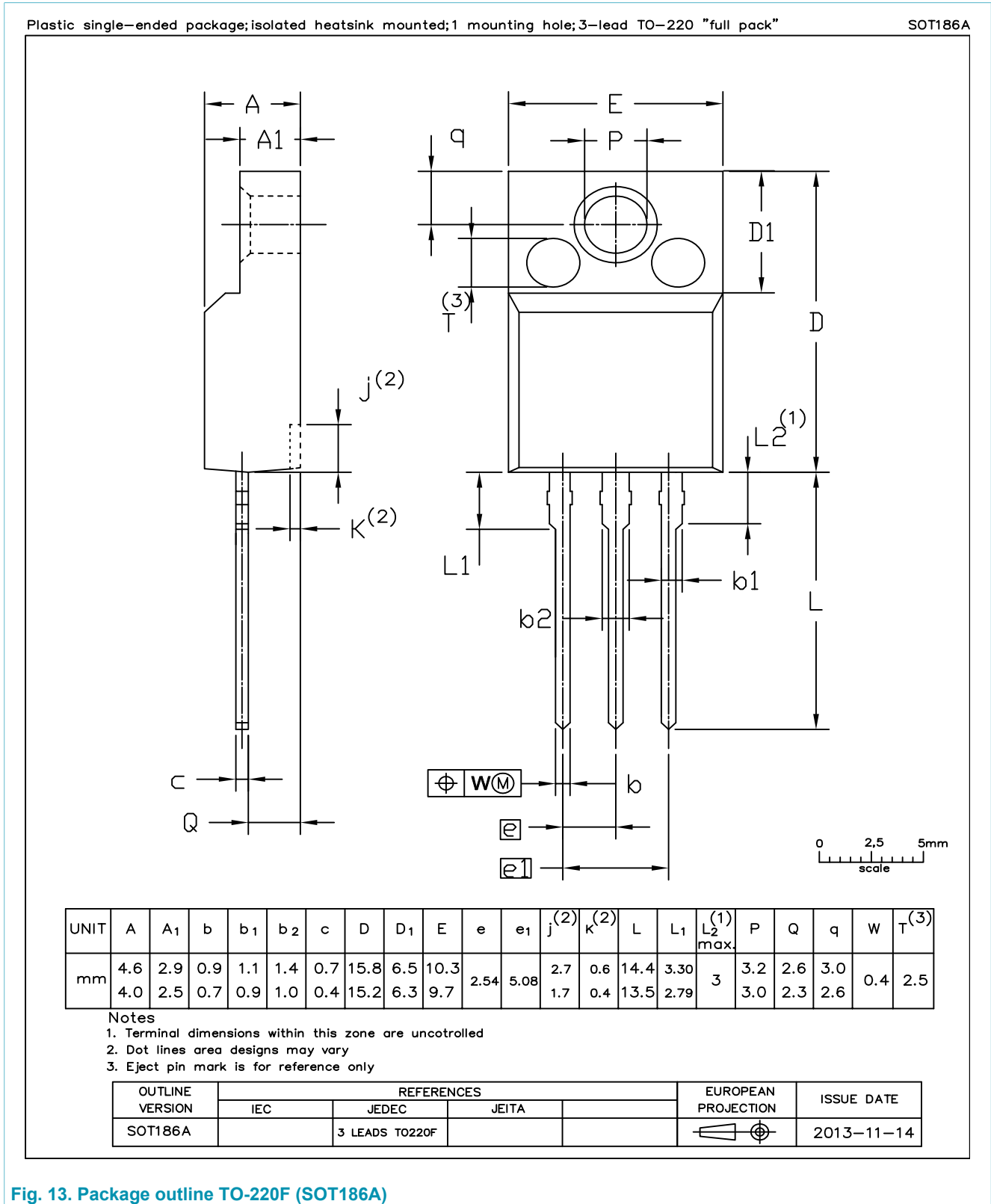


Fig. 13. Package outline TO-220F (SOT186A)

## 13. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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